

**The University of Portland  
Donald P. Shiley School of Engineering**

**EE371  
Lab #2  
Design Project  
CE Amplifier Frequency Response**

**Assigned:** Wed, Feb 19, 2020  
**Lab Checkoffs due:** Wed, Mar 18, 2020  
**Final Report Due:** Mon, Mar 22, 2020 (in EE352 class)

Your task is to independently design, build and test a single-stage PNP Common Emitter Amplifier circuit (CE Amp) as shown in Figure 1. (Note the external  $R_s$  resistor; please don't forget this). Figure 2 shows the front-end 10-to-1 attenuator input circuit that you should use in this lab (similar to Lab1). Your job is to determine all four unknown resistor component values in this circuit such that the following specifications are met:

1.  $|A_M| \geq 125V/V$
2.  $\omega_L \leq 2\pi(100\text{Hz})$
3.  $\omega_H \geq 2\pi(225\text{kHz})$
4.  $P_{DC} \leq 35\text{mW}$
5.  $I_C \geq 0.5\text{mA}$
5. Achieve nominal bias stability to temperature and  $\beta$  variation

**You are required to:**

1. Design a CE Amplifier circuit (i.e., determine all four unknown resistor values; see Figure 1) which meets all the design specifications listed above using the Hand-design techniques learned in class.
2. Verify your Hand-design using PSPICE simulation (AC Sweep and Bias Point Details).
3. Build, test and experimentally demonstrate your design in the Lab using your Lab Kit.
4. Record all your Hand, PSPICE and Lab values in the attached Summary Table.
5. Properly record all your Lab results and scratch calculations in your Lab Notebook (as usual) following the guidelines described in Lab1.
6. Get your Lab circuit checked-off by the Instructor.
7. Each student is required to write a their own Formal Lab Report with your final Summary Table included. Your Lab Report should follow the guidelines described in this document and in the Lab2 Final Report Grading Rubric (see website).

**Circuit Design:**

1. For your circuit design, refer to Figure 1.
2. You will use a 2N3906 PNP BJT transistor. A 2N3906 datasheet is attached for your reference.
3. For Hand analysis, assume the following PNP transistor parameters:  $\beta=200$ ,  $V_A=I_C/h_{oe}$  where  $h_{oe}=25\mu\text{mhos}$ ,  $V_{BE-on}=0.7\text{V}$ ,  $V_T=25\text{mV}$ .
4. For PSPICE simulation, use a QbreakP3 and assume the following PNP transistor parameters:  $\beta_F=200$ ,  $V_{AF}=I_C/h_{oe}$ , where  $h_{oe}=25\mu\text{mhos}$ ,  $T_F=600\text{pS}$ ,  $M_{JC}=0$ ,  $M_{JE}=0$ ,  $C_{JC}=C_{obo}$  from datasheet, and  $C_{JE}=C_{ibo}$  from the datasheet. Perform AC Sweep Analysis with Bias Point Details on.
5. Perform DC Hand analysis to start your circuit design and set your four resistor values ( $R_E$ ,  $R_C$ ,  $R_1$ , and  $R_2$ ). Remember to follow the "1/3-rule" and the "1/10-rule". After this, you **must re-do your hand calculations precisely** and record in your Summary Table. Verify that you met the bias stability requirement to Temperature and  $\beta$  variation. Specifically, precisely re-

calculate all DC node voltages, branch currents and  $P_{DC}$ . Verify your DC Hand analysis in PSPICE (Bias Points Details). Record your results in your Summary Table.

6. Perform small-signal AC full Frequency Response Hand and PSPICE analyses to complete your circuit design. Calculate  $A_M$ ,  $R_{in}$ ,  $R_{out}$ ,  $\omega_L$  and  $\omega_H$ . Note that you can calculate  $R_{in}$  and  $R_{out}$  with Hand analysis only; you cannot calculate  $R_{in}$  and  $R_{out}$  with PSPICE since you cannot run Transfer Function Analysis on this circuit. For Hand analysis, you will need to perform SCTC and OCTC analyses as shown in class. Note that you first need to determine  $C_\pi$  (using the " $C_\pi$ -equation"),  $C_\mu$ ,  $g_m$ ,  $r_\pi$ ,  $r_o$  and  $f_t$ . You will need to consult the attached 2N3906 datasheet. For PSPICE simulation, you will need to perform AC Sweep with Bias Points Details. Record your results in your Summary Table.

### Lab Experimentation:

1. **Measure and record  $\beta$**  of your 2N3906 PNP transistor using your DMM.
2. Build and test your circuit in the Lab using your Lab Kit. Use the front-end 10-to-1 attenuator input circuit as shown in Figure 2. **IMPORTANT: "Stagger"** the base and collector/emitter leads of your 2N3906 in your board-layout as explained in class.
3. **Measure and record all DC values.** As in Lab1, you should first build your circuit at home ("Manhattan" layout) and then verify all DC values. This will allow you to be much more efficient and less stressed in the Lab where you will do the more complex AC measurements ( $A_M$ ,  $R_{in}$ ,  $R_{out}$ ,  $\omega_L$  and  $\omega_H$ ) using the Function Generator and the Oscilloscope.
4. **Determine the small-signal AC frequency values ( $A_M$ ,  $\omega_H$  and  $\omega_L$ )** of your circuit in the Lab by monitoring on the scope the p-p amplitudes of  $v_{out}$  and  $v_{in}$ . See Figure 2 for the  $v_{in}$  circuit. Specifically, **first, measure and record  $A_M$**  by setting the function generator amplitude such that you obtain an approximate 1V p-p amplitude at  $v_{out}$  at 10KHz (mid-band frequency) and then precisely measure  $v_{out}$  using "Cursors". Then precisely measure  $v_{in}$  using "Cursors". Then calculate  $A_M=v_{out}/v_{in}$ . **Second, measure and record  $\omega_L=2\pi f_L$**  by setting  $v_{out}$  to 1V p-p precisely at 10kHz using "Measure" and then adjusting the input frequency down (below 100Hz) until the amplitude of the output reaches  $-3dB$  (or  $1/\sqrt{2}V=0.707V$ ) using "Measure". **Third, similarly measure and record  $\omega_H=2\pi f_H$**  by setting  $v_{out}$  to 1V p-p precisely at 10kHz using "Measure" and then adjusting the input frequency up (above 200KHz) until the amplitude of the output again reaches  $-3dB$  (or  $1/\sqrt{2}V=0.707V$ ) using "Measure".
5. **Determine the small-signal AC  $R_{in}$  and  $R_{out}$**  in the Lab using the technique described in the attached sheet (similar to Lab1).
6. Enter all your Lab data in your Lab Notebook as usual.
7. **Fill-in your Summary Table** (attached) with all your Hand, PSPICE, and Lab values.
8. **Get your lab circuit checked-off** by the Instructor.

### Lab Report:

1. Your Formal Lab Report should be typed, double-spaced, neat, professional, concise and clear. It should contain the following sections:
  - 1) Title Page
  - 2) Executive Summary
  - 3) Hand design and analysis discussion (refer to attachment)
  - 4) PSPICE simulation discussion (refer to attachment)
  - 5) Lab results discussion (refer to Summary Table)
  - 6) Conclusions
  - 7) Summary Table (type-writtent)
  - 8) Attachment: Hand design and analysis (both DC and AC). Include final schematic.
  - 9) Attachment: PSPICE simulation printouts (annotated).
  - 10) Attachment: Copy of your signed lab notebook "check-off" page.
2. More specifically, your Lab Report should include the following:

- 1) A neat sketch of your final CE Amplifier circuit design schematic with all circuit component values clearly labeled.
- 2) Your DC hand and PSPICE analyses and Lab results. Label and circle all DC operating point node voltages and branch currents directly on your circuit schematic. Briefly show how you met the bias stability requirement.
- 3) Your small-signal AC Mid-Band Hand analysis and Lab results for  $R_{in}$  and  $R_{out}$ .
- 4) Your small-signal AC full Frequency Response Hand and PSPICE analyses and Lab results for  $A_M$ ,  $\omega_L=2\pi f_L$ , and  $\omega_H=2\pi f_H$ . For your Hand analysis, you will use the SCTC and OCTC equations as shown in class. For PSPICE simulation, you should perform AC Sweep Analysis with Bias Point Details turned on.
- 5) All PSPICE simulation printouts which verify all your Hand-design calculations above (except for  $R_{in}$  and  $R_{out}$  which cannot be done in PSPICE). You should hand-in your PSPICE schematic, Bode Plots and an edited xxx.out file. Please label/annotate all your PSPICE printouts appropriately, as usual.
- 6) Your completed and type-written Summary Table with Hand, PSPICE and Lab values.

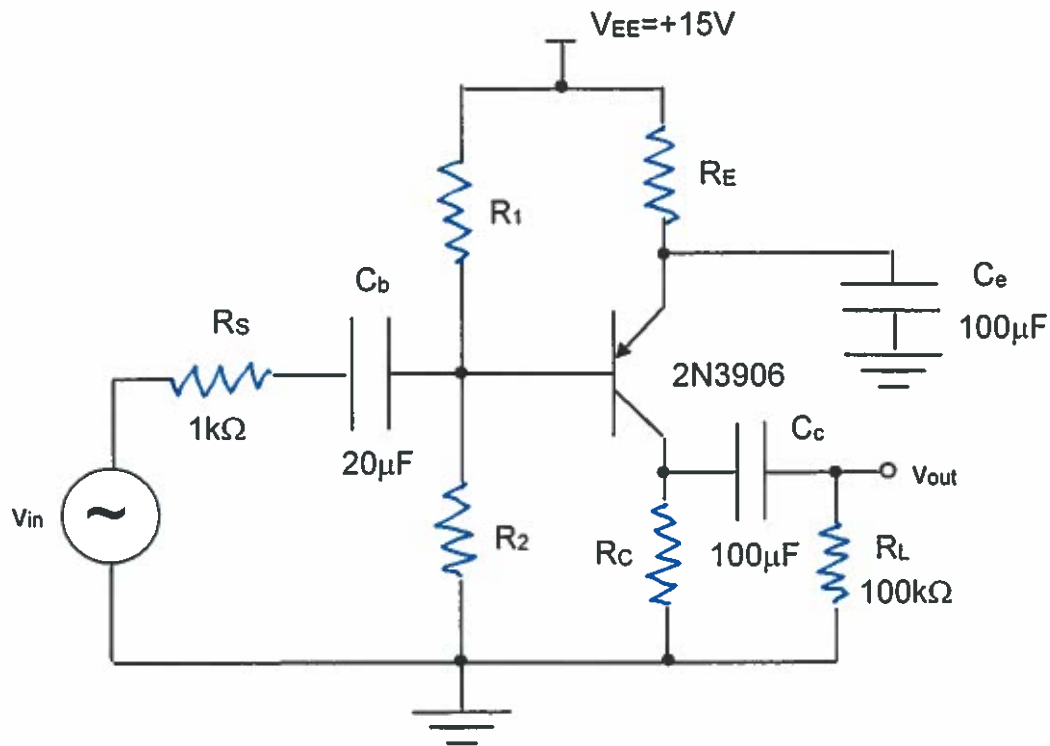


Figure 1.

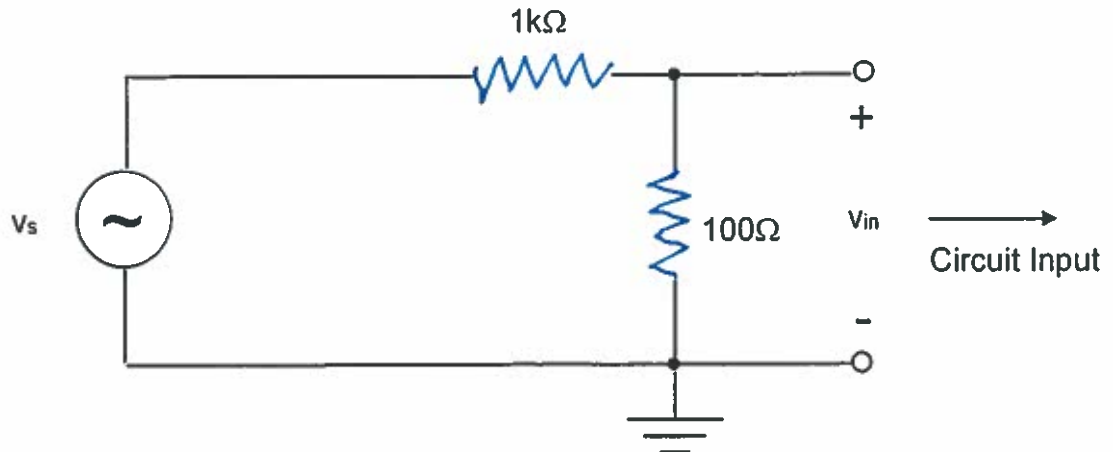
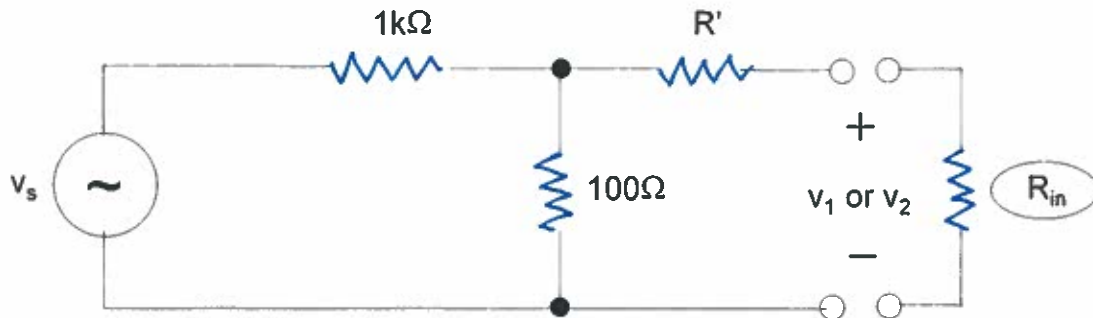


Figure 2.

## R<sub>in</sub> and R<sub>out</sub> Measurements

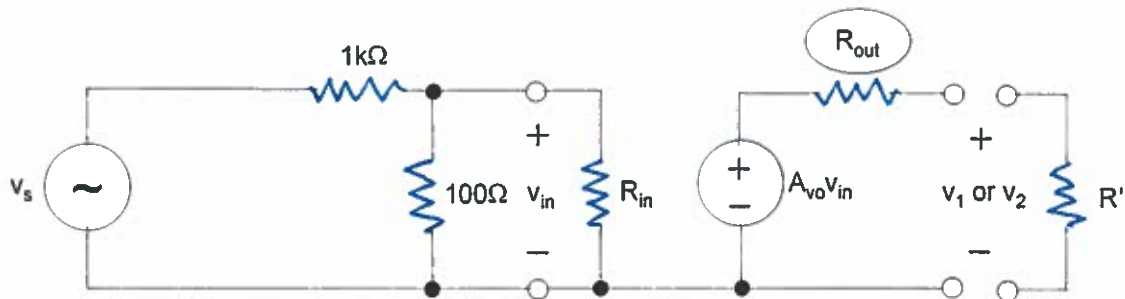
### 1) R<sub>in</sub> Measurement:



- Select  $R' \approx R_{in}$  (expected).
- Replace the  $R_s$  1k $\Omega$  resistor with your  $R'$  as shown above. Set  $v_s$  such that  $v_2 \approx 50\text{mV}$  p-p and approximately 10kHz. Accurately measure  $v_2$  and record.
- With the input source circuit (including  $R'$ ) disconnected from  $R_{in}$ , accurately measure the resulting open-circuit voltage of the input source circuit,  $v_1$ , and record.
- Calculate  $R_{in}$  as follows:

$$R_{in} = R' \frac{v_2}{v_1 - v_2}$$

### 2) R<sub>out</sub> Measurement:



- Select  $R' \approx R_{out}$  (expected). Remove  $R_L$  from circuit. Return the  $R_s$  1k $\Omega$  resistor back in the circuit.
- With  $R'$  connected to the output (i.e., in parallel with  $R_c$ ), set  $v_s$  such that  $v_2 = v_{out} \approx 0.5\text{V}$  p-p with an approximate frequency of 10kHz. Accurately measure  $v_2$  and record.
- Disconnect  $R'$  and accurately measure the resulting open-circuit output voltage,  $v_1$ , and record.
- Calculate  $R_{out}$  as follows:

$$R_{out} = R' \frac{v_1 - v_2}{v_2}$$

2N3905/2N3906 General-Purpose *pnp* Transistors\*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CE0}$	40	Vdc
Collector-Base Voltage	$V_{CB0}$	40	Vdc
Emitter-Base Voltage	$V_{EB0}$	5.0	Vdc
Collector Current — Continuous	$I_C$	200	mA <sub>dc</sub>
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	825 5.0	mW mW/°C
Total Power Dissipation @ $T_A = 80^\circ\text{C}$	$P_D$	250	mW
Total Device Dissipation @ $T_C = 75^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.6 12	Watts mW/°C
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	°C

\*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

**2N3905**  
**2N3906**

CASE 29-02, STYLE 1  
TO-92 (TO-226AA)

GENERAL PURPOSE  
TRANSISTOR

PNP SILICON

ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage(I) ( $I_C = 1.0 \text{ mA}_{dc}, I_B = 0$ )	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ( $I_C = 10 \mu\text{A}_{dc}, I_E = 0$ )	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10 \mu\text{A}_{dc}, I_C = 0$ )	$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current ( $V_{CE} = 30 \text{ Vdc}, V_{BE} = 3.0 \text{ Vdc}$ )	$I_{DL}$	—	50	nA <sub>dc</sub>
Collector Cutoff Current ( $V_{CE} = 30 \text{ Vdc}, V_{BE} = 3.0 \text{ Vdc}$ )	$I_{CEX}$	—	50	nA <sub>dc</sub>

ON CHARACTERISTICS(I)

DC Current Gain ( $I_C = 0.1 \text{ mA}_{dc}, V_{CE} = 1.0 \text{ Vdc}$ )	2N3905 2N3906	$h_{FE}$	30 60	—	—
( $I_C = 1.0 \text{ mA}_{dc}, V_{CE} = 1.0 \text{ Vdc}$ )	2N3905 2N3906		40 60	—	—
( $I_C = 10 \text{ mA}_{dc}, V_{CE} = 1.0 \text{ Vdc}$ )	2N3905 2N3906		50 100	150 300	—
( $I_C = 50 \text{ mA}_{dc}, V_{CE} = 1.0 \text{ Vdc}$ )	2N3905 2N3906		30 60	—	—
( $I_C = 100 \text{ mA}_{dc}, V_{CE} = 1.0 \text{ Vdc}$ )	2N3905 2N3906		15 30	—	—
Collector-Emitter Saturation Voltage ( $I_C = 10 \text{ mA}_{dc}, I_B = 1.0 \text{ mA}_{dc}$ ) ( $I_C = 50 \text{ mA}_{dc}, I_B = 5.0 \text{ mA}_{dc}$ )		$V_{CE(sat)}$	— —	0.26 0.4	Vdc
Base-Emitter Saturation Voltage ( $I_C = 10 \text{ mA}_{dc}, I_B = 1.0 \text{ mA}_{dc}$ ) ( $I_C = 50 \text{ mA}_{dc}, I_B = 5.0 \text{ mA}_{dc}$ )		$V_{BE(sat)}$	0.65 —	0.85 0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ( $I_C = 10 \text{ mA}_{dc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$ )	2N3905 2N3906	$f_T$	200 250	—	MHz
Output Capacitance ( $V_{CO} = 5.0 \text{ Vdc}, I_E = 0, f = 100 \text{ kHz}$ )		$C_{ob0}$	—	4.5	pF

2N3905, 2N3906

ELECTRICAL CHARACTERISTICS (continued) (T<sub>A</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Input Capacitance (V <sub>BE</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 100 kHz)	C <sub>ibo</sub>	—	10.0	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>ie</sub>	0.5 2.0	8.0 12	k ohms
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>re</sub>	0.1 0.1	5.0 10	X 10 <sup>-4</sup>
Small-Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	50 100	200 400	—
Output Admittance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>oe</sub>	1.0 3.0	40 60	μmhos
Noise Figure (I <sub>C</sub> = 100 μA, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 k ohm, f = 10 Hz to 15.7 kHz)	NF	—	5.0 4.0	dB

SWITCHING CHARACTERISTICS

Characteristic	Conditions	Symbol	Min	Max	Unit
Delay Time	V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = 0.5 Vdc I <sub>C</sub> = 10 mA, I <sub>B1</sub> = 1.0 mA	t <sub>d</sub>	—	35	ns
Rise Time		t <sub>r</sub>	—	35	ns
Storage Time	V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mA, I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mA	t <sub>s</sub>	—	200	ns
Fall Time		t <sub>s</sub>	—	225	ns
		t <sub>f</sub>	—	60	ns
		t <sub>f</sub>	—	75	ns

(1) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

\*Courtesy of Motorola, used by permission.

## Lab #2 Summary Table

Parameter	Hand	PSPICE	Lab
$I_E$			
$I_B$			
$I_C$			
$V_E$			
$V_B$			
$V_C$			
$I_{R1}$			
$I_{R2}$			
$V_{BE-ON}$			
$P_{DC}$			
$A_M$			
$\omega_L = 2\pi f_L$			
$\omega_H = 2\pi f_H$			
$R_{in}$		N/A	
$R_{out}$		N/A	
$V_A$			N/A
$\beta$			
$g_m$			
$\Gamma_\pi$			
$\Gamma_o$			N/A
$C_\pi$			N/A
$C_\mu$			N/A
$f_T$			N/A